

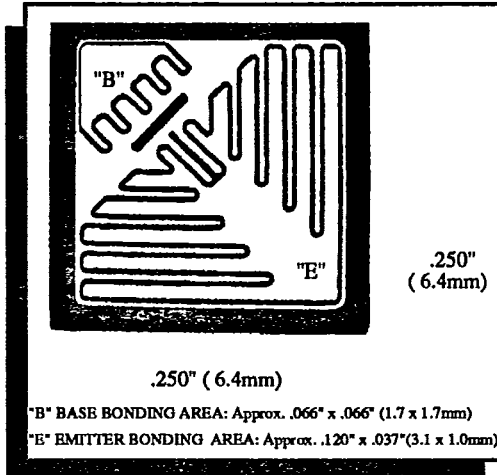


# CCC6003

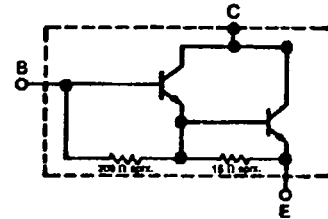
## 15 A, 550 V, NPN Darlington Power Transistor Chip

- Triple Diffused, Glass Passivated
- Contact Metallization: Base and emitter-aluminum  
Collector (Al-Ti-Ni-Au)
- Assembly Recommendations:  
Base and emitter-15-mil aluminum wire bond  
Collector-mounted with Pb/Sn preform
- Chip thickness- $12 \pm 2$  mils ( $300 \pm 50$  microns)
- Reference device types:

PTC6000  
PTC6001  
PTC6002  
PTC6003



### Equivalent Circuit:



### Electrical Characteristics At 25°C

The chip is 100% probed to the conditions and limits specified.

CHARACTERISTIC	TEST CONDITIONS				LIMITS		UNITS
	VOLTAGE V dc		CURRENT A dc		MIN.	MAX.	
	V <sub>CE</sub>	V <sub>BB</sub>	I <sub>C</sub>	I <sub>B</sub>			
V <sub>CEO</sub> (sus)**			1		500		V
I <sub>CBO</sub>	550					500	μA
I <sub>BBO</sub>		4				300	mA
V <sub>CE</sub> (sat)*			15	1.5		2.0	V
h <sub>FE</sub> *	5		15		20	60	

\*Pulsed: pulse duration = 300μs, duty factor < 2%.

\*\*Performed on assembled device evaluation samples only. This voltage MUST NOT be measured on a curve tracer.

### POWER TECHNOLOGY COMPONENTS a Microsemi Company

23201 SOUTH NORMANDIE AVENUE • TORRANCE, CALIFORNIA 90501  
(213) 534-3737 • TELEX 664276 • FAX (213) 530-5609